**Product data sheet** 

# 1. General description

PNP low  $V_{CEsat}$  transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4140T-Q

## 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- · High efficiency due to less heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

# 3. Applications

- · General-purpose switching and muting
- LCD backlighting
- Supply line switching circuits
- · Battery-driven equipment (mobile phones, video cameras and handheld devices)

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-40	V
I <sub>C</sub>	collector current		-	-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-2	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	300	500	mΩ



40 V, 1 A PNP low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	Е	emitter		C 
3	С	collector		В—
			1 2	E sym132
			SOT23	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PBSS5140T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23

# 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
PBSS5140T-Q	%2Н

[1] % = placeholder for manufacturing site code

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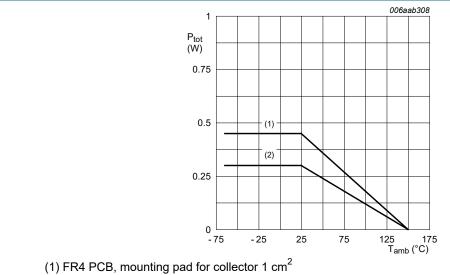
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-40	V
$V_{CEO}$	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-2	Α
I <sub>BM</sub>	peak base current			-	-1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	450	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1  $\rm cm^2$ .



- (2) FR4 PCB, standard footprint

Power derating curves

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
11(J-a)	thermal resistance from	in free air	[1]	-	-	417	K/W
	junction to ambient		[2]	-	-	278	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

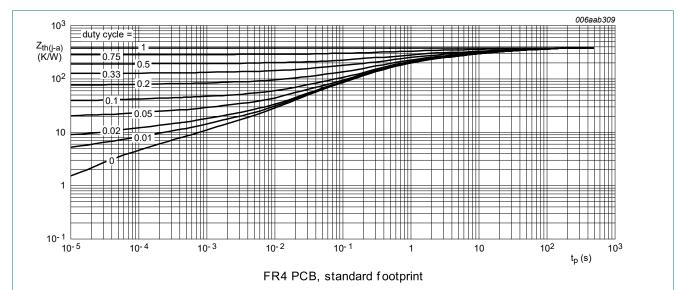


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

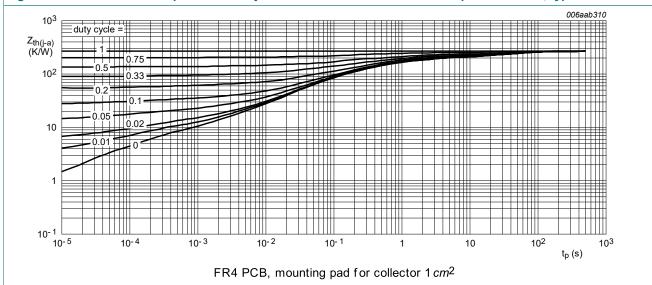


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -40 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -40 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CEO</sub>	collector-emitter cut-off current (base open)	I <sub>B</sub> = 0 A; V <sub>CE</sub> = -30 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>ЕВО</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -1 mA; T <sub>amb</sub> = 25 °C	300	-	-	
		V <sub>CE</sub> = -5 V; I <sub>C</sub> = -100 mA; T <sub>amb</sub> = 25 °C	300	-	800	
		$V_{CE}$ = -5 V; $I_{C}$ = -500 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	250	-	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	160	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -100 mA; I <sub>B</sub> = -1 mA; T <sub>amb</sub> = 25 °C	-	-	-200	mV
		$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-250	mV
		$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-500	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	300	500	mΩ
$V_{BEsat}$	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -1 A; T <sub>amb</sub> = 25 °C	-	-	-1	V
$t_d$	delay time	V <sub>CC</sub> = -10 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -25 mA;	-	10	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 25 mA; T <sub>amb</sub> = 25 °C	-	31	-	ns
t <sub>on</sub>	turn-on time		-	41	-	ns
t <sub>s</sub>	storage time		-	195	-	ns
t <sub>f</sub>	fall time		-	65	-	ns
t <sub>off</sub>	turn-off time		-	260	-	ns
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -50 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	150	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	12	pF

### 40 V, 1 A PNP low VCEsat transistor

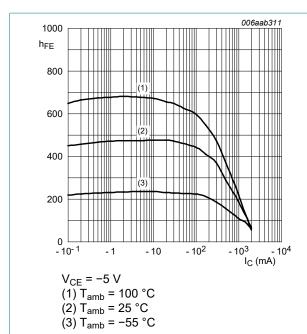


Fig. 4. DC current gain as a function of collector current; typical values

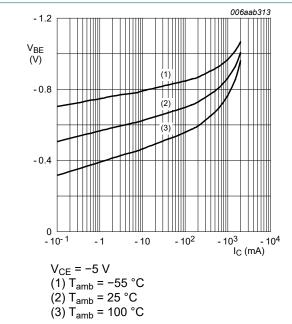


Fig. 6. Base-emitter voltage as a function of collector current; typical values

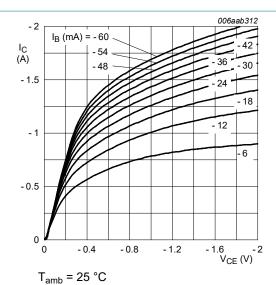
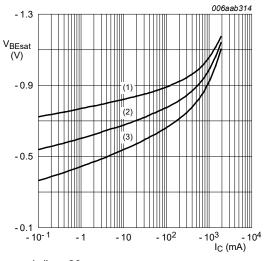


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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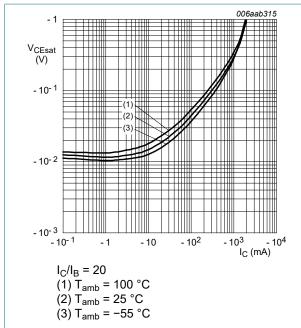


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

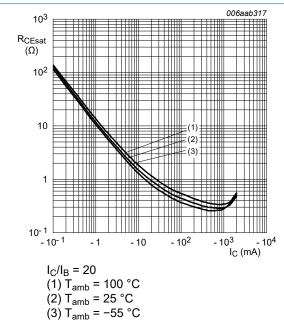


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

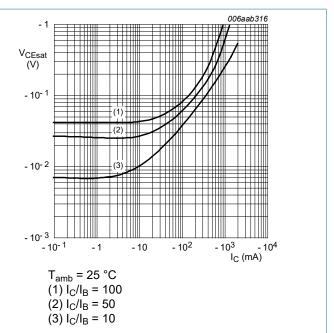


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

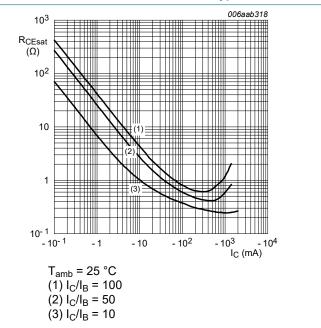
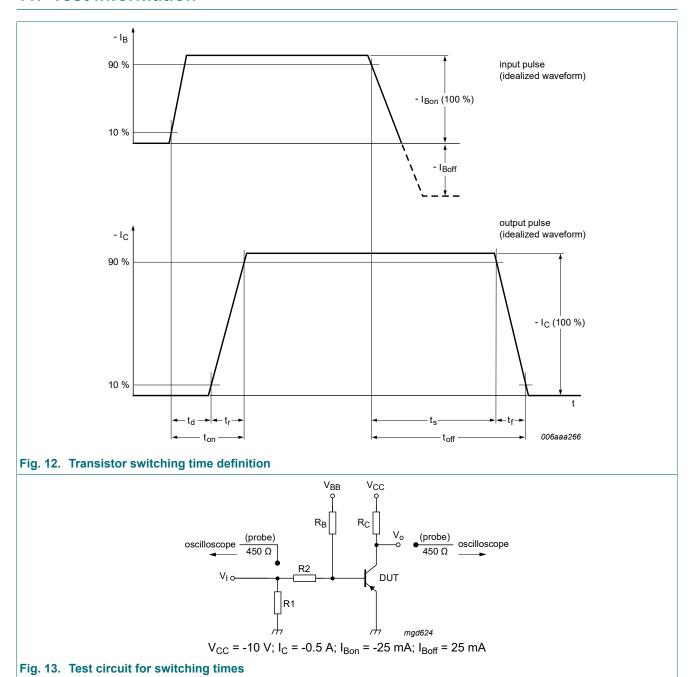


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

40 V, 1 A PNP low VCEsat transistor

# 11. Test information

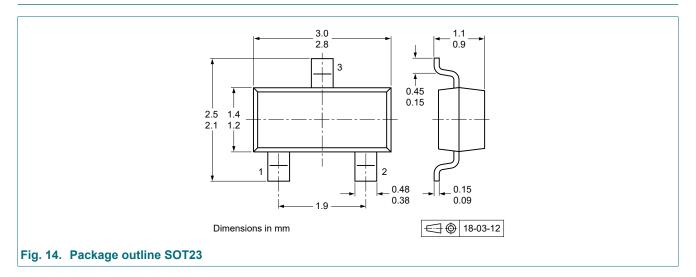


### **Quality information**

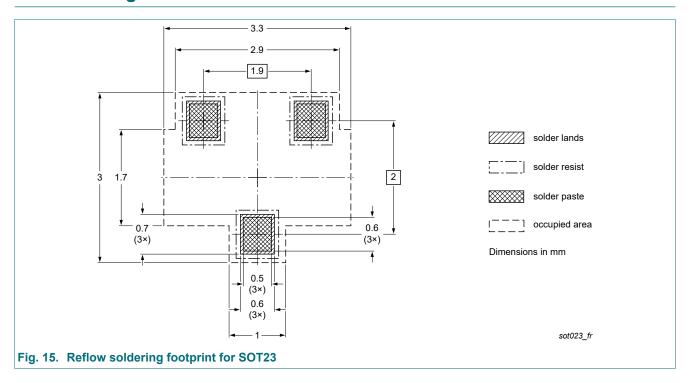
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

40 V, 1 A PNP low VCEsat transistor

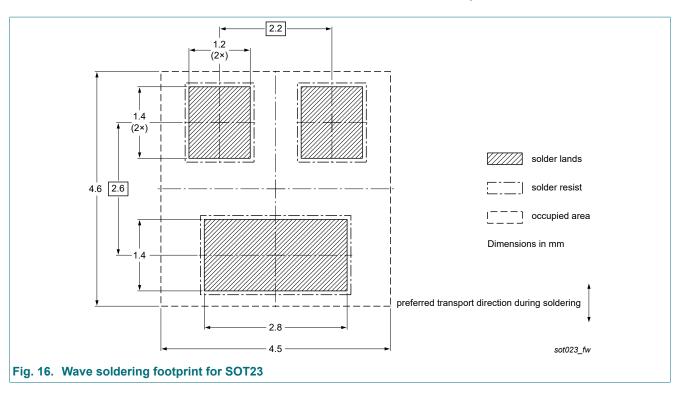
# 12. Package outline



# 13. Soldering



# 40 V, 1 A PNP low VCEsat transistor



40 V, 1 A PNP low VCEsat transistor

# 14. Revision history

## Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5140T-Q v.1	20231004	Product data sheet	-	-

## 40 V, 1 A PNP low VCEsat transistor

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# PBSS5140T-Q

# 40 V, 1 A PNP low VCEsat transistor

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